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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Sunkara et al.)
)
Filed: November 10, 2003) Examiner:
) Group Art Unit:
Serial No: 10/705,687)
)
For: BULK SYNTHESIS OF METAL AND METAL,)
BASED DIELECTRIC NANOWIRES)
)
Atty. Docket No.: AD138/2001)

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INFORMATION DISCLOSURE DOCUMENT

Enclosed is a list and copies of references considered by Applicant to be pertinent in the
examination of the above-identified patent application.

Applicant submits this Information Disclosure Statement in accordance with the duty of
disclosure under 37CFR §1.56 and 1.97-1.98. This Statement is filed in accordance with 37 CFR
§1.97(b)(3), prior to issuance of a First Office.

Applicants(s) submitted herewith patents, publications or other information of which they
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Respectfully submitted,

A handwritten signature in black ink, appearing to read "David W. Carrithers", written over a horizontal line.

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OTHER PRIOR ART (Including Author, Title, Date Pertinent Pages, ETC.)

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Examiner Signature	/Edward M. Johnson/ (06/24/2007)	Date Considered	
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